

Silicon NPN Power Transistors

2N6121 2N6122 2N6123

DESCRIPTION

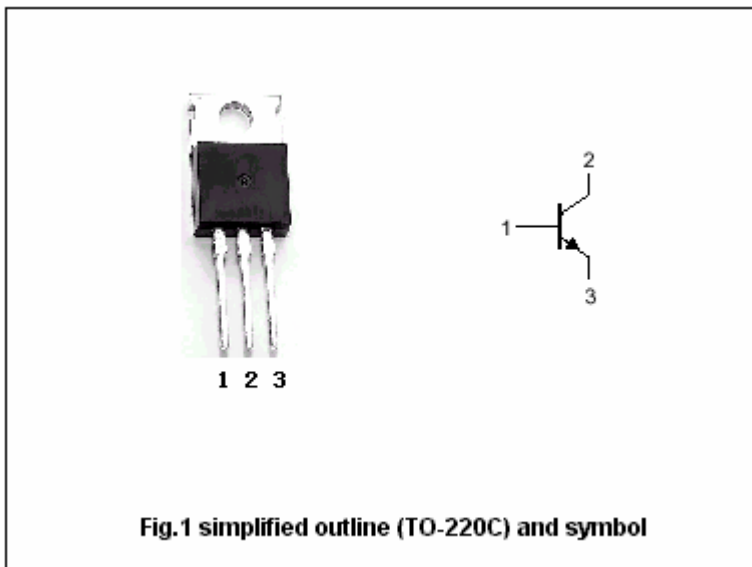
- With TO-220 package
- Complement to PNP type :
2N6124 ;2N6125 ;2N6126

APPLICATIONS

- For use in power amplifier and switching circuit applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6121	45	V
		2N6122	60	
		2N6123	80	
V_{CEO}	Collector-emitter voltage	2N6121	45	V
		2N6122	60	
		2N6123	80	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_{CM}	Collector current-peak		8	A
I_B	Base current		1	A
P_T	Total power dissipation	$T_C=25$	40	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	3.125	/W

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CHARACTERISTICS

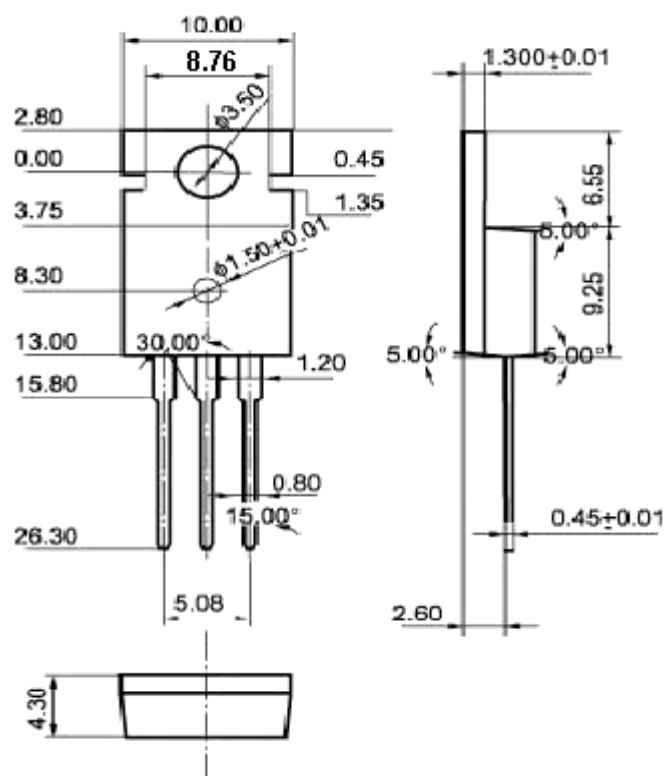
T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(SUS)}	Collector-emitter sustaining voltage	2N6121	I _C =0.1A ; I _B =0	45			V
		2N6122		60			
		2N6123		80			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =1.5A ; I _B =0.15A			0.6	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =4.0A ; I _B =1.0A			1.4	V
V _{BE}	Base-emitter on voltage		I _C =1.5A ; V _{CE} =2V			1.2	V
I _{CEX}	Collector cut-off current	2N6121	V _{CE} =45V ; V _{BE} =1.5V T _C =125			0.1 2.0	mA
		2N6122	V _{CE} =60V ; V _{BE} =1.5V T _C =125			0.1 2.0	
		2N6123	V _{CE} =80V ; V _{BE} =1.5V T _C =125			0.1 2.0	
I _{CEO}	Collector cut-off current	2N6121	V _{CE} =45V ; I _B =0			1.0	mA
		2N6122	V _{CE} =60V ; I _B =0				
		2N6123	V _{CE} =80V ; I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =5V ; I _C =0			1.0	mA
h _{FE-1}	DC current gain	2N6121	I _C =1.5A ; V _{CE} =2V	25		100	
		2N6122					
		2N6123		20		80	
h _{FE-2}	DC current gain	2N6121	I _C =4A ; V _{CE} =2V	10			
		2N6122					
		2N6123		7			
f _T	Transition frequency		I _C =1A ; V _{CE} =4V	2.5			MHz

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)